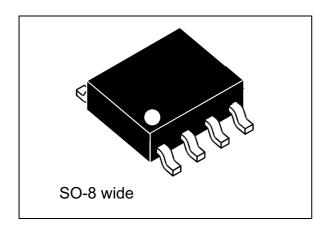


Protection IC for ringing SLICs

Datasheet - production data



Features

- · Protection IC recommended for ringing SLICs
- Wide firing voltage range: -120 V to +120 V
- Low gate triggering current: I_G = 5 mA max
- Peak pulse current: $I_{PP} = 50 \text{ A} (10/1000 \mu \text{s})$
- Holding current: I_H = 150 mA min.

Applications

- · Dual battery supply voltage SLICs
- Central office (CO)
- Private branch exchange (PBX)
- Digital loop carrier (DLC)
- Digital subscriber line access multiplexer (DSLAM)
- Fiber in the loop (FITL)
- Wireless local loop (WLL)
- Hybrid fiber coax (HFC)
- ISDN terminal adapter
- Cable modem

Description

The LCP22 has been developed to protect SLICs operating on both negative and positive battery supplies, as well as high voltage SLICs. It provides crowbar mode protection for both TIP and RING lines. The surge suppression is assumed for each wire by two thyristor structures, one dedicated to positive surges the second one for negative surges. Both positive and negative threshold levels are programmable by two gates.

LCP22 can be used to help equipment to meet various standards such as UL1950, IEC 60950 / CSAC22.2, UL1459 and TIA-968-A. LCP22 pinout and clearance is compatible with UL60950. A Trisil ™ meets UL94 V0.

The LCP22 associated with Epcos PTC model B59173C1130A151 is compliant with ITU TK20/K21 (4 kV lightning and AC power fault tests).

Figure 1. Functional diagram

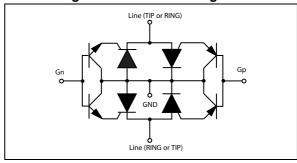
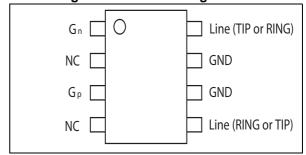


Figure 2. Pin-out configuration



TM: Trisil is a trademark of STMicroelectronics

Characteristics LCP22

1 Characteristics

Table 1. Compliant with the following standards

Standard	Peak surge voltage (V)	Voltage waveform	Required peak current (A)	Current waveform	Minimum series resistor Rs to meet standard (Ω)
GR-1089 Core First level	2500	2/10 µs	500	2/10 μs	12
Cit 1000 Colo 1 ii St level	1000	10/1000 µs	100	10/1000 µs	10
GR-1089 Core Second level	5000	2/10 µs	500	2/10 µs	24
GR-1089 Core Intra-building	1500	2/10 µs	100	2/10 µs	0
	6000		150		35
ITU-T-K20/K21	4000	10/700 μs	100	5/310 µs	10
	1500		37.5		0
ITU-T-K20 (IEC61000-4-2)	8000	1/60 ns	ESD contact discharge		0
110-1-R20 (IEG01000-4-2)	15000	1/00 113	ESD air	discharge	0
IEC61000-4-5	4000	10/700 µs	100	5/310 µs	14
IEC61000-4-5	4000	1.2/50 µs	100	8/20 µs	0
TIA 969-A (formarly ECC part 69) type A	1500	10/160 µs	200	10/160 µs	20
TIA-968-A (formerly FCC part 68) type A	800	10/560 µs	100	10/560 µs	15
TIA-968-A (formerly FCC part 68) type B	1000	9/720 µs	25	5/320 µs	0

Table 2. Absolute maximum ratings (T_{amb} = 25 °C)

Symbol	Parameter	Value	Unit	
I _{PP}	Peak pulse current	50 80 150	А	
I _{TSM}	Non repetitive surge peak on-state current (F = 50 Hz) $I_{TSM} \text{ value specified for each line} I_{TSM} \text{ value can be applied on both lines at the same time} I_{p} = 0.2 \text{ s} t_{p} = 1 \text{ s} t_{p} = 15 \text{ min.}$			А
V _{Gn} V _{Gp}	Negative battery voltage range Positive battery voltage range			V
Тј	Operating junction temperature range			°C
T _{stg}	Storage temperature range	-55 to +150	°C	
T _L	Lead solder temperature (10 s duration)		260	°C

LCP22 Characteristics



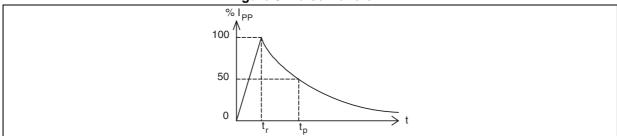


Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
R _{th(j-a)}	Junction to ambient	150	°C/W

Table 4. Parameters related to the negative suppressor

Symbol	Parameter	Test conditions	Min.	Max.	Unit
I _{Gn}	Negative gate trigger current	V _{Gn/GND} = -60 V Measured at 50 Hz		5	mA
I _{H-}	Holding current (see Figure 4)	V _{Gn} = -60 V	150		mA
V _{DGL} -	Dynamic switching voltage Gn / TIP or RING ⁽¹⁾	$V_{Gn/GND}$ = -60 V 10/700 µs 2 kV R _s = 25 Ω I _{PP} = 30 A 1.2/50 µs 2 kV R _s = 25 Ω I _{PP} = 30 A		8 12	V
V _{GnT}	G _n to TIP voltage	I _{Gn} = 20 mA	0.7	1.7	٧

^{1.} The V_{DGL} value is the difference between the peak line voltage during the surge and the programmed gate voltage.

Table 5. Parameters related to the positive suppressor

Symbol	Parameter	Test conditions	Min.	Max.	Unit
I_{Gp}	Positive gate trigger current	V _{Gp/GND} = 60 V, measured at 50 Hz		5	mA
V _{DGL+}	Dynamic switching voltage Gp / TIP or RING ⁽¹⁾	$V_{Gp/GND} = 60 \text{ V}$ $10/700 \mu\text{s} 2 \text{ kV} R_{s} = 25 \Omega I_{PP} = 30 \text{ A}$ $1.2/50 \mu\text{s} 2 \text{ kV} R_{s} = 25 \Omega I_{PP} = 30 \text{ A}$		8 20	V
V_{GpR}	G _P to RING voltage	I _{Gp} = -20 mA	1	2	V

^{1.} The V_{DGL} value is the difference between the peak line voltage during the surge and the programmed gate voltage.

Table 6. Parameters related to TIP or RING / GND

Symbol	Parameter	Test conditions	Min.	Max.	Unit
I _R	Reverse leakage current	$V_{TIP \text{ or RING}} = +120 \text{ V}$ $V_{Gp/TIP \text{ or RING}} = +1 \text{ V}$ $V_{TIP \text{ or RING}} = -120 \text{ V}$ $V_{Gn/TIP \text{ or RING}} = -1 \text{ V}$		5 5	μΑ
С	Capacitance TIP or RING / GND	$V_R = -3 \text{ V}, \text{ F} = 1 \text{ MHz}, V_{Gp} = 60 \text{ V}, V_{Gn} = -60 \text{ V}$		60	pF

Characteristics LCP22

Table 7. Recommended gate capacitance

Symbol	Component	Min.	Тур.	Max.	Unit
C _n , C _p	Gate decoupling capacitance	100	220		nF

Figure 4. Relative variation of holding current versus junction temperature

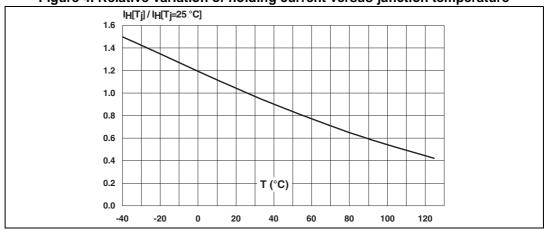


Figure 5. Maximum non repetitive surge peak on state current versus overload duration

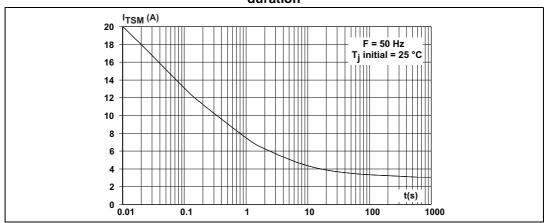
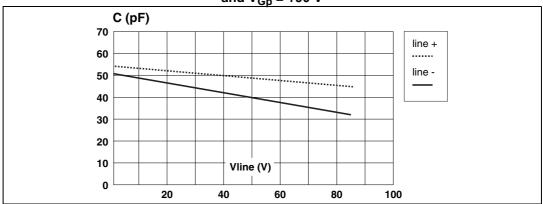


Figure 6. Capacitance versus reverse applied voltage (typical values) with V_{Gn} = -90 V and V_{Gp} = +90 V



LCP22 **Technical information**

Technical information 2

L1 O TIP IGp Gn -Vbat +Vh GND O Cn 7/17 o GND L2 0 //// ↑_{V Ring}

Figure 7. LCP22 concept behavior

Figure 7 shows the classical protection circuit using the LCP22 crowbar concept. This topology has been developed to protect two-battery voltage SLICs. It allows both positive and negative firing thresholds to be programmed. The LCP22 has two gates (Gn and Gp). Gn is biased to negative battery voltage -Vbat, while Gp is biased to the positive battery voltage +Vb.

When a negative surge occurs on one wire (L1 for example), a current IGn flows through the base of the transistor T1 and then injects a current in the gate of the thyristor Th1 which turns-on. All the surge current flows through the ground. After the surge, when the current flowing through Th1 becomes less negative than the negative holding current I_{H-}, Th1 switches off. This holding current I_{H-} is temperature dependent as per Figure 4

When a positive surge occurs on one wire (L1 for example), a current IGp flows through the base of the transistor T2 and then injects a current in the gate of the thyristor Th2 which fires. All the surge current flows through the ground. After the surge, when the current flowing through Th2 becomes less positive than the positive holding current I_{H+}, Th2 switches off. This holding current I_{H+}, typically 20 mA at 25 °C, is temperature dependent and the same Figure 4 also applies.

The capacitors Cn and Cp are used to speed up the crowbar structure firing during the fast rise or fall edges. This allows minimization of the dynamic breakover voltage at the SLIC TIP and RING inputs during fast surges. Please note that these capacitors are generally available around the SLIC. To be efficient they have to be as close as possible to the LCP22 gate pins (Gn and Gp) and to the reference ground track (or plan). The optimized value for Cn and Cp is 220 nF.

The series resistors Rs shown in Figure 7 represent the fuse resistors or the PTCs which are needed to withstand the power contact or the power induction tests imposed by the country standards. Taking this factor into account, the actual lightning surge current flowing through the LCP22 is equal to:

I surge = Vsurge / (Rg + Rs)

With

V surge = peak surge voltage imposed by the standard.

Rg = series resistor of the surge generator

Rs = series resistor of the line card (e.g. PTC)

LCP22 **Technical information**

> For a line card with 50 Ω of series resistors which has to be qualified under GR-1089 1000 V 10/1000 µs surge, the present current through the LCP22 is equal to:

I surge =
$$1000 / (10 + 50) = 17 A$$

Rs (*) = PTC or Resistor fuse

The LCP22 topology is particularly optimized for the new telecom applications such as fiber in the loop, WLL systems, and decentralized central office, for example.

Line card -Vbat Rs (*) TIP Gn TIP **GND** 220nF LCP22 Line **SLIC** 220nF **RING** Rs (*) RING Thi +Vb

Figure 8. Protection of SLIC with positive and negative battery voltages

Figure 8 shows the classical protection topology for SLIC using both positive and negative battery voltages. With such a topology the SLIC is protected against surge over +Vb and lower than -Vbat. In this case, +Vb can be programmed up to +120 V while -Vbat can be programmed down to -120 V.

LCP22 Package information

3 Package information

- Epoxy meets UL94, V0
- Lead-free package

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

D A2 A K E A1 C

Figure 9. SO-8 wide dimension definitions

Package information LCP22

Table 8. SO-8 wide dimension values

	Dimensions					
Ref.		Millimeters			Inches	
	Min.		Max.	Min.		Max.
Α	1.70	1.90	2.10	0.07	0.07	0.08
A1	0.05	0.10	0.25	0.00	0.00	0.01
A2	1.65	1.80	1.75	0.06	0.07	0.07
b	0.38	0.43	0.48	0.01	0.02	0.02
С	0.15	0.20	0.25	0.01	0.01	0.01
D	5.14	5.24	5.34	0.02	0.021	0.21
Е	5.20	5.30	5.40	0.02	0.021	0.21
E1	7.70	7.80	8.25	0.30	0.031	0.32
е		1.27		0.05	0.05	
K			8.00	0.14	0.31	
L	0.55	0.75	0.85	0.02	0.03	0.03

Figure 10. SO-8 wide footprint in mm (inches)

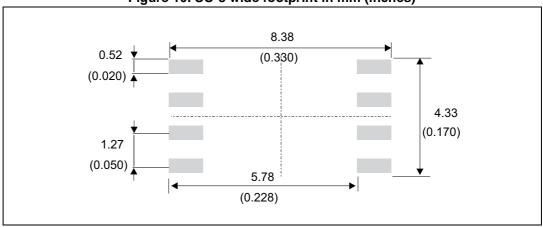
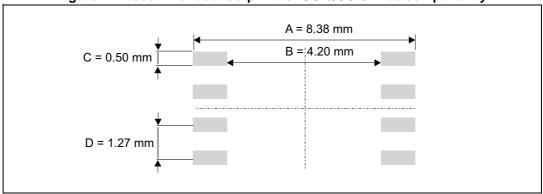


Figure 11. Recommended footprint for SO-8/SO-8 wide compatibility



4 Ordering information

Table 9. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
LCP22-150B1RL	LCP22	SO-8 wide	0.125g	1500	Tape and reel

5 Revision history

Table 10. Document revision history

Date	Revision	Changes		
07-Feb-2014	1	nitial release.		
03-Jun-2014	2	Updated Figure 1: Functional diagram, Figure 2: Pin-out configuration and T_j value in Table 2: Absolute maximum ratings $(T_{amb} = 25 \ ^{\circ}\text{C})$.		
22-Oct-2014	3	Added Figure 11.		

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